



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Diodes

BAW567DW Multi-Chip DIODES

FEATURES

Power dissipation

P_{CM} : 0.2 W ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 150 mA

Collector-base voltage

V_R : 75 V

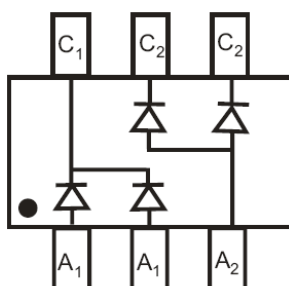
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-363



MARKING:KAC



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR) R}$	$I_R = 2.5\mu A$	75			V
Reverse voltage leakage current	I_R	$V_R = 75V$ $V_R = 20V$			2.5 0.025	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$			0.715 0.855 1.0 1.25	V
Junction capacitance	C_j	$V_R = 0V$ $f = 1MHz$		2		pF

Typical Characteristics

BAW567DW

